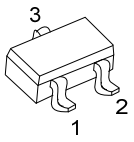
BAS70xW

DIODE

SCHOTTKY BARRIER DIODES



SOT-323

■ DESCRIPTION

Planar Schottky barrier diodes encapsulated in the SOT-323 small plastic SMD package. Single diode and dual diodes with different pin configuration are available.

■ FEATURES

* Low Turn-on voltage
* Fast switching
* Ultra-small surface mount package
* Also available in lead free version

■ ORDERING INFORMATION

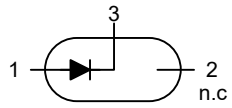
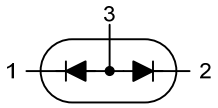
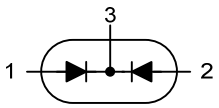
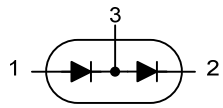
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BAS70WL-AL3-R	BAS70WG-AL3-R	SOT-323	A	NC	K	Tape Reel
BAS70AWL-AL3-R	BAS70AWG-AL3-R	SOT-323	K1	K2	A1A2	Tape Reel
BAS70CWL-AL3-R	BAS70CWG-AL3-R	SOT-323	A1	A2	K1K2	Tape Reel
BAS70SWL-AL3-R	BAS70SWG-AL3-R	SOT-323	A1	K2	K1A2	Tape Reel

Note: Pin Assignment: A: Anode K: Cathode NC: No Connection

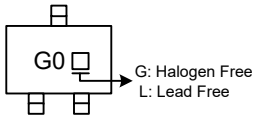
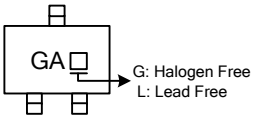
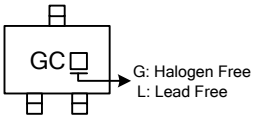
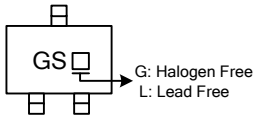
BAS70xWG-AL3-R
(1) Packing Type
(2) Package Type
(3) Green Package
(4) Diode Configuration

(1) R: Tape Reel
(2) AL3: SOT-323
(3) G: Halogen Free and Lead Free, L: Lead Free
(4) x: refer to DIODE CONFIGURATION AND SYMBOL

■ DIODE CONFIGURATION AND SYMBOL

BAS70W	BAS70AW	BAS70CW	BAS70SW
			

■ MARKING

BAS70W	BAS70AW	BAS70CW	BAS70SW
			

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■ ABSOLUATE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

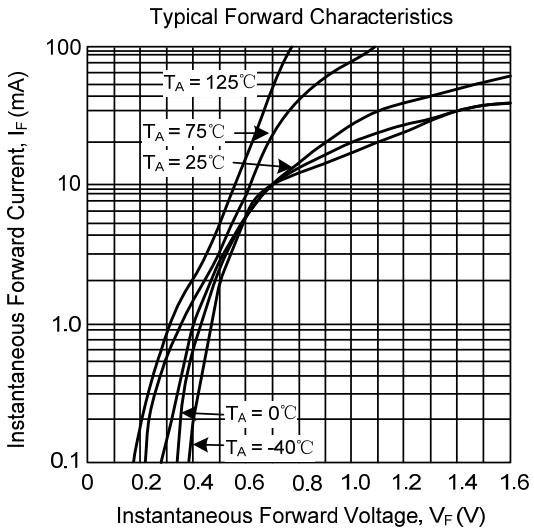
PARAMETER	SYMBOL	RATINGS	UNITS
DC Voltage	V_R	70	V
Forward Continuous Current	I_F	70	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	-55 ~ +150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

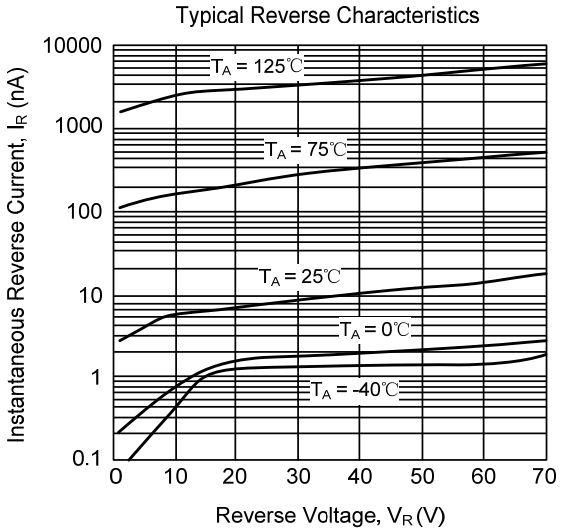
Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

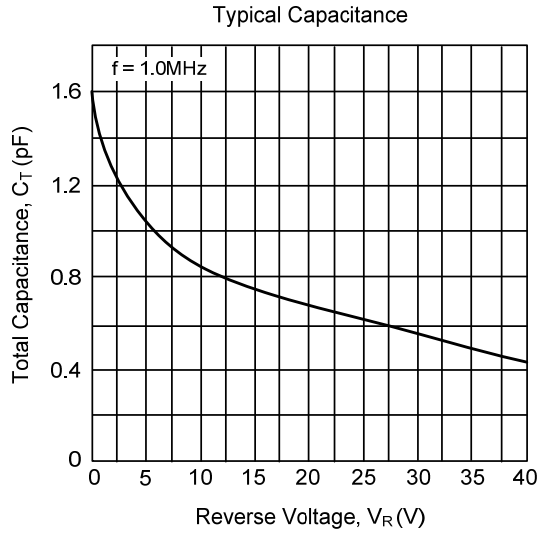
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

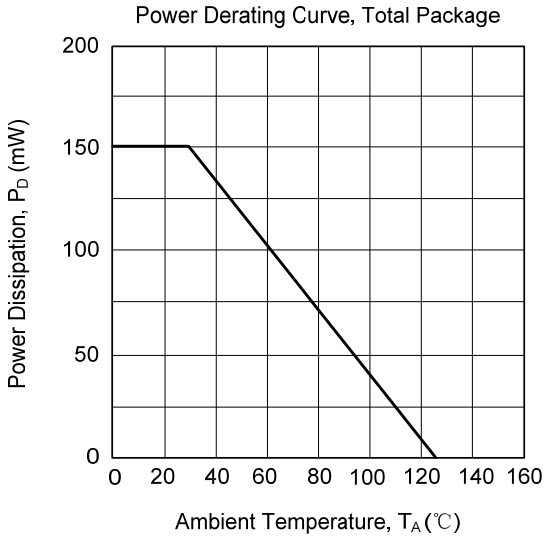
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage	BV_R	I_R= 10μA	70			V
Reverse Voltage Leakage Current	I_R	V_R=50V			200	nA
Forward Voltage	V_F	I_F=1mA			410	mV
		I_F=15mA			1000	mV
Diode Capacitance	C_D	V_R=0V, f=1MHz			2	pF
Reveres Recovery Time	t_{RR}	I_F=I_R=10mA, I_{RR}=0.1xI_R, R_L=100Ω			5	nS

■ TYPICAL CHARACTERISTICS









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